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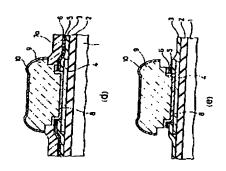
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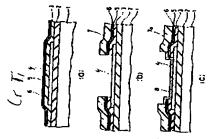
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TITLE

MANUFACTURE OF

SEMICONDUCTOR DEVICE





ABSTRACT: PURPOSE: To prevent corrosion of a pad electrode consisting of AI or the like by a method wherein a bump type electrode layer is formed on an adhesion barrier metal layer by an electrolytic plating method and the metal layer is removed using this electrode layer as a mask.

> CONSTITUTION: A silicon oxide film 2 is formed on the whole surface of a semiconductor substrate 1 and an Al pad electrode 4 is selectively formed on this film 2. After that, an insulating film 3, such as a silicon oxide film and the like, is formed on the whole surface including the electrode 4 and metal layers 5 and 6 are formed in order on this film 3. Then, after a P-type photosensitive resin film 7 is formed on the whole surface, the region, where is located on the electrode 4, of the film 7 is selectively opened. A plurality of the metal layers 5 and 6 and the film 3 are etched away in order to make the electrode 4 expose. Then, parts, which match to a first opening part of a first mask, of the layers 5 and 6 are removed, then, an adhesion barrier metal layer 8 is formed in a second opening part of a second mask. In this case, the layer 8 is superposed on the edge parts, which are located on the sides of the opening parts, of the layers 5 and 6 at its edge parts and the layer 8 and the layers 5 and 6 are electrically connected to each other. Thereby, corrosion of a pad electrode is avoided.

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